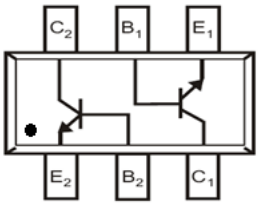
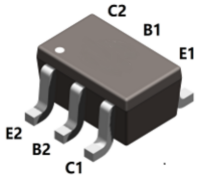
MMDT2222A

Dual NPN General Purpose Transistor

Features

- Epitaxial planar die construction
- Complementary PNP type available MMDT2907A
- Ultra-small surface mount package





SOT-363

Mechanical Data

- Case: SOT-363
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMDT2222A	SOT-363	3000 pcs / Tape & Reel	K1P

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (Continuous)	I_C	0.6	A
Collector Current (Peak)	I_{CM}	1.2	A
Continuous Base Current	I_B	0.15	A
Peak Base Current	I_{BM}	0.2	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation *1	P_D	0.2	W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	625	°C/W
Thermal Resistance Junction-to-Air *2	$R_{\theta JA}$	260	°C/W
Thermal Resistance Junction-to-Case *2	$R_{\theta JC}$	200	°C/W
Thermal Resistance Junction-to-Lead *2	$R_{\theta JL}$	220	°C/W
Ambient Temperature	T_A	-55 ~ +150	°C
Operating Junction Temperature	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

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Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	75	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	6	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB} = 60V, I_E = 0	-	-	10	nA
		V_{CB} = 60V, I_E = 0, T_J = 150°C	-	-	10	μA
Collector Cut-off Current	I_{CEX}	V_{CE} = 60V, $V_{EB(OFF)}$ = 3V	-	-	10	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 3V, I_C = 0	-	-	10	nA
Base Cut-off Current	I_{BL}	V_{CE} = 60V, $V_{EB(OFF)}$ = 3V	-	-	20	nA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 0.1mA	35	-	-	-
		V_{CE} = 10V, I_C = 1mA	50	-	-	-
		V_{CE} = 10V, I_C = 10mA	75	-	-	-
		V_{CE} = 10V, I_C = 150mA	100	-	300	-
		V_{CE} = 10V, I_C = 500mA	40	-	-	-
		V_{CE} = 10V, I_C = 10mA, T_J = -55°C	50	-	-	-
		V_{CE} = 1V, I_C = 150mA	35	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 150mA, I_B =15mA	-	-	0.3	V
		I_C = 500mA, I_B = 50mA	-	-	1.0	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 150mA, I_B =15mA	0.6	-	1.2	V
		I_C = 500mA, I_B = 50mA	-	-	2.0	V
Base-Emitter Voltage	$V_{BE(on)}$	I_C = 200mA, V_{CE} = 10V	-	-	1	V
Transition Frequency	f_T	I_C = 20mA, V_{CE} = 20V f = 100MHz	300	-	-	MHz
Collector Output Capacitance	C_{OBO}	V_{CB} = 10V, I_E = 0, f = 1MHZ	-	-	8	pF
Noise Figure	N_F	V_{CE} = 10V, f = 1.0kHz I_C = 100mA, R_S = 1.0kΩ	-	-	4.0	dB
Delay Time	t_d	V_{CC} = 30V, $V_{BE(OFF)}$ = 0.5V I_C = 150mA, I_{B1} = 15mA	-	-	10	ns
Rise Time	t_r		-	-	25	ns
Storage Time	t_s	V_{CC} = 30V,I_C = 150mA I_{B1} = I_{B2} = 15mA	-	-	225	ns
Fall Time	t_f		-	-	60	ns

Notes:

1. Device mounted on a minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.
2. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

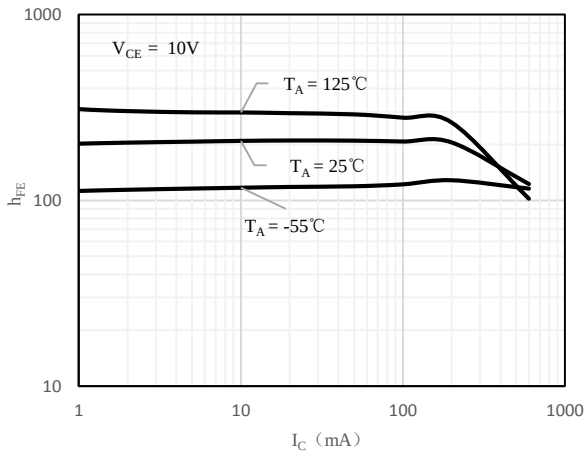

Fig 1 h_{FE} vs. I_C

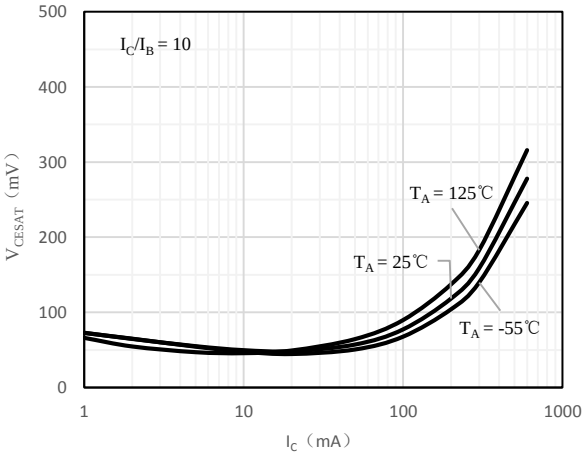

Fig 2 $V_{CE(sat)}$ vs. I_C

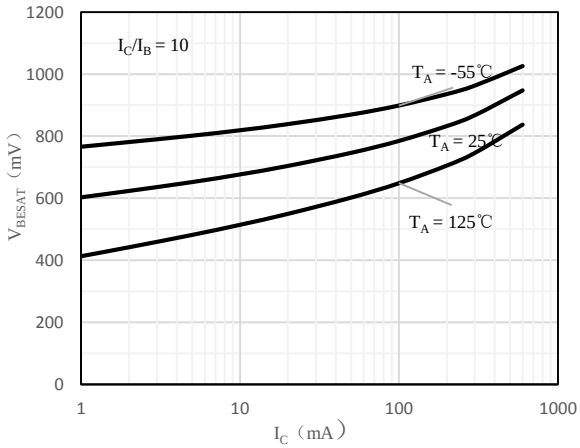

Fig 3 $V_{BE(sat)}$ vs. I_C

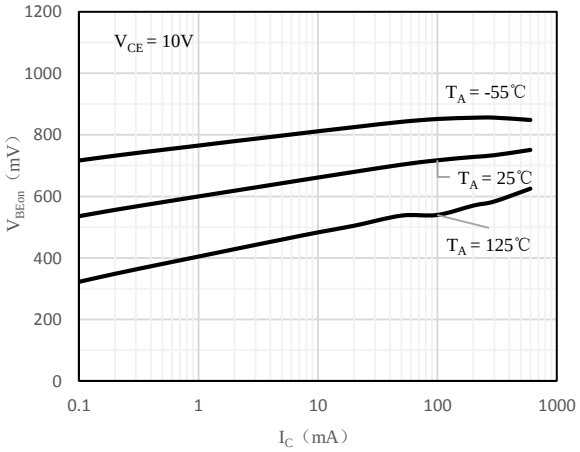

Fig 4 $V_{BE(ON)}$ vs. I_C

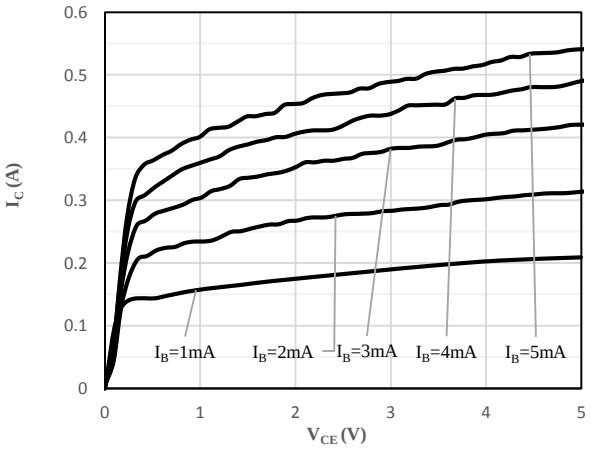

Fig 5 I_C vs. V_{CE}

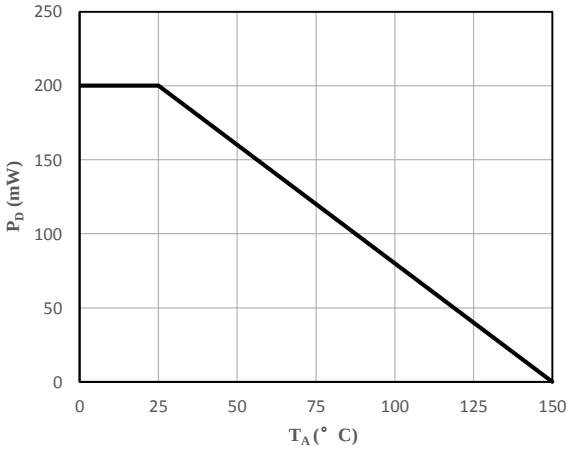

Fig 6 P_D vs. T_A

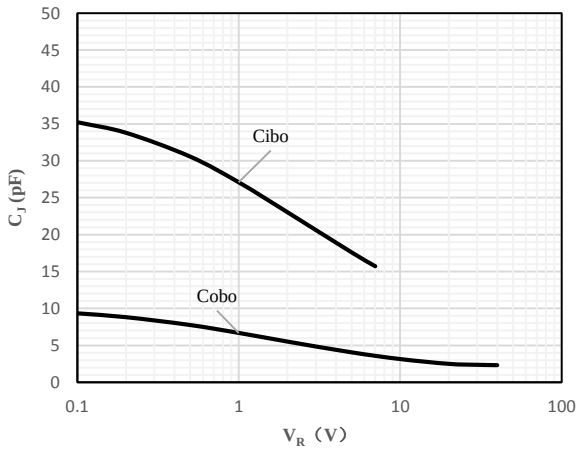

Fig 7 C_J vs. V_R

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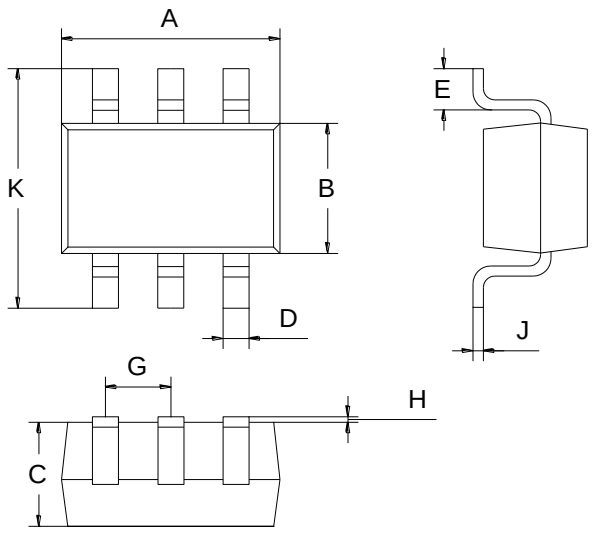
Package Outline Dimensions (Unit: mm)



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Dimension	**Min.**	**Max.**
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

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